

Cong Ye

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/987237/publications.pdf>

Version: 2024-02-01

46
papers

1,397
citations

304743

22
h-index

330143

37
g-index

46
all docs

46
docs citations

46
times ranked

1743
citing authors

#	ARTICLE	IF	CITATIONS
1	A high-performance self-powered broadband photodetector based on a $\text{CH}_3\text{NH}_3\text{PbI}_3$ perovskite/ZnO nanorod array heterostructure. <i>Journal of Materials Chemistry C</i> , 2016, 4, 7302-7308.	5.5	159
2	Role of Oxygen Vacancies at the $\text{TiO}_2/\text{HfO}_2$ Interface in Flexible Oxide-Based Resistive Switching Memory. <i>Advanced Electronic Materials</i> , 2019, 5, 1800833.	5.1	105
3	Physical Mechanism and Performance Factors of Metal Oxide Based Resistive Switching Memory: A Review. <i>Journal of Materials Science and Technology</i> , 2016, 32, 1-11.	10.7	94
4	Low-power bipolar resistive switching $\text{TiN}/\text{HfO}_2/\text{ITO}$ memory with self-compliance current phenomenon. <i>Applied Physics Express</i> , 2014, 7, 034101.	2.4	70
5	Designing High-Performance Storage in $\text{HfO}_2/\text{BiFeO}_3$ Memristor for Artificial Synapse Applications. <i>Advanced Electronic Materials</i> , 2020, 6, 1901012.	5.1	66
6	HfO_2 -Based Memristor as an Artificial Synapse for Neuromorphic Computing with Tri-Layer $\text{HfO}_2/\text{BiFeO}_3/\text{HfO}_2$ Design. <i>Advanced Functional Materials</i> , 2021, 31, 2107131.	14.9	63
7	High performance, self-powered ultraviolet photodetector based on a ZnO nanoarrays/GaN structure with a CdS insert layer. <i>New Journal of Chemistry</i> , 2017, 41, 4901-4907.	2.8	58
8	Charge Quantity Influence on Resistance Switching Characteristic During Forming Process. <i>IEEE Electron Device Letters</i> , 2013, 34, 502-504.	3.9	55
9	Enhanced resistive switching performance for bilayer $\text{HfO}_2/\text{TiO}_2$ resistive random access memory. <i>Semiconductor Science and Technology</i> , 2016, 31, 105005.	2.0	49
10	Origin of Hopping Conduction in Sn-Doped Silicon Oxide RRAM With Supercritical CO_2 Fluid Treatment. <i>IEEE Electron Device Letters</i> , 2012, 33, 1693-1695.	3.9	45
11	Bilayered Oxide-Based Cognitive Memristor with Brain-Inspired Learning Activities. <i>Advanced Electronic Materials</i> , 2019, 5, 1900439.	5.1	43
12	High-performance ultraviolet-visible tunable perovskite photodetector based on solar cell structure. <i>Science China Materials</i> , 2017, 60, 407-414.	6.3	42
13	Optoelectronic Artificial Synapses Based on Two-Dimensional Transitional-Metal Trichalcogenide. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 30797-30805.	8.0	41
14	Composition dependence of band alignment and dielectric constant for $\text{Hf}_{1-x}\text{Ti}_x\text{O}_2$ thin films on Si (100). <i>Journal of Applied Physics</i> , 2010, 107, 104103.	2.5	38
15	$\text{C}_2\text{N}/\text{BlueP}$ van der Waals hetero-structure: an efficient photocatalytic water splitting 2D material. <i>Physical Chemistry Chemical Physics</i> , 2020, 22, 1485-1492.	2.8	34
16	Resistive switching performance improvement of InGaZnO-based memory device by nitrogen plasma treatment. <i>Journal of Materials Science and Technology</i> , 2020, 49, 1-6.	10.7	33
17	Black Phosphorus Based Multicolor Light-Modulated Transparent Memristor with Enhanced Resistive Switching Performance. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 25108-25114.	8.0	32
18	Flexible Poly(Vinyl Alcohol)-Graphene Oxide Hybrid Nanocomposite Based Cognitive Memristor with Pavlovian-Conditioned Reflex Activities. <i>Advanced Electronic Materials</i> , 2020, 6, 1901402.	5.1	31

#	ARTICLE	IF	CITATIONS
19	Negative differential resistance behavior in phosphorus-doped armchair graphene nanoribbon junctions. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	26
20	Exploring the role of nitrogen incorporation in ZrO ₂ resistive switching film for enhancing the device performance. <i>Journal of Alloys and Compounds</i> , 2019, 775, 1301-1306.	5.5	26
21	An indirect way to achieve comprehensive performance improvement of resistive memory: when hafnium meets ITO in an electrode. <i>Nanoscale</i> , 2020, 12, 3267-3272.	5.6	23
22	Improved thermal stability, interface, and electrical properties of HfO ₂ films prepared by pulsed laser deposition using <i>in situ</i> ionized nitrogen. <i>Applied Physics Letters</i> , 2009, 95, .	3.3	22
23	Boosting the performance of resistive switching memory with a transparent ITO electrode using supercritical fluid nitridation. <i>RSC Advances</i> , 2017, 7, 11585-11590.	3.6	21
24	A Robust and Low-Power Bismuth Doped Tin Oxide Memristor Derived from Coaxial Conductive Filaments. <i>Small</i> , 2020, 16, e2004619.	10.0	21
25	Memristor Based on TiO _x /Al ₂ O ₃ Bilayer as Flexible Artificial Synapse for Neuromorphic Electronics. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 375-379.	3.0	21
26	Phosphorus-doping-induced rectifying behavior in armchair graphene nanoribbons devices. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	18
27	The electronic transport behavior of hybridized zigzag graphene and boron nitride nanoribbons. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	18
28	Improved performance of ITO/TiO ₂ /HfO ₂ /Pt random resistive accessory memory by nitrogen annealing treatment. <i>Microelectronics Reliability</i> , 2016, 57, 34-38.	1.7	15
29	High Voltage Gain WSe ₂ Complementary Compact Inverter With Buried Gate for Local Doping. <i>IEEE Electron Device Letters</i> , 2020, 41, 944-947.	3.9	14
30	Exploration of highly enhanced performance and resistive switching mechanism in hafnium doping ZnO memristive device. <i>Semiconductor Science and Technology</i> , 2018, 33, 085013.	2.0	13
31	Evidence of interface conversion and electrical characteristics improvement of ultra-thin HfTiO films upon rapid thermal annealing. <i>Applied Physics Letters</i> , 2011, 99, 182904.	3.3	11
32	Topochemical Synthesis of Copper Phosphide Nanoribbons for Flexible Optoelectronic Memristors. <i>Advanced Functional Materials</i> , 0, , 2110900.	14.9	11
33	Effect of sputtering atmosphere on the characteristics of ZrO _x resistive switching memory. <i>Semiconductor Science and Technology</i> , 2017, 32, 055016.	2.0	10
34	Impact of Forming Compliance Current on Storage Window Induced by a Gadolinium Electrode in Oxide-Based Resistive Random Access Memory. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 96-100.	3.0	10
35	Hafnium nanocrystals observed in a HfTiO compound film bring about excellent performance of flexible selectors in memory integration. <i>Nanoscale</i> , 2019, 11, 20792-20796.	5.6	10
36	Two-Dimensional As/BlueP van der Waals Hetero-Structure as a Promising Photocatalyst for Water Splitting: A DFT Study. <i>Coatings</i> , 2020, 10, 1160.	2.6	9

#	ARTICLE	IF	CITATIONS
37	Dielectric property and electrical conduction mechanism of ZrO ₂ –TiO ₂ composite thin films. Journal of Materials Science: Materials in Electronics, 2012, 23, 174-179.	2.2	8
38	Brain-like synaptic memristor based on lithium-doped silicate for neuromorphic computing. Frontiers of Physics, 2022, 17, .	5.0	8
39	Drive current and hot carrier reliability improvements of high-aspect-ratio n-channel fin-shaped field effect transistor with high-tensile contact etching stop layer. Applied Physics Letters, 2011, 99, .	3.3	7
40	Black phosphorus field effect transistors stable in harsh conditions via surface engineering. Applied Physics Letters, 2020, 117, .	3.3	7
41	Growth and magnetic properties of single crystalline Ni nanowire arrays prepared by pulse DC electrodeposition. Science China: Physics, Mechanics and Astronomy, 2011, 54, 1244-1248.	5.1	6
42	Flexible HfO ₂ /Graphene Oxide Selector With Fast Switching and High Endurance. IEEE Journal of the Electron Devices Society, 2019, 7, 1125-1128.	2.1	3
43	An improved analytical model for the statistics of SET emergence point in HfO ₂ memristive device. AIP Advances, 2019, 9, 025118.	1.3	1
44	EFFECT OF GATE ELECTRODES ON STRUCTURE AND ELECTRICAL PROPERTIES OF SPUTTERED HfO ₂ THIN FILMS. Modern Physics Letters B, 2012, 26, 1250161.	1.9	0
45	Influence of Source and Drain Electrodes on Device Performance of ZnO Thin Film Transistors. Integrated Ferroelectrics, 2013, 142, 73-78.	0.7	0
46	Topochemical Synthesis of Copper Phosphide Nanoribbons for Flexible Optoelectronic Memristors (Adv. Funct. Mater. 14/2022). Advanced Functional Materials, 2022, 32, .	14.9	0